

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD531

DESCRIPTION

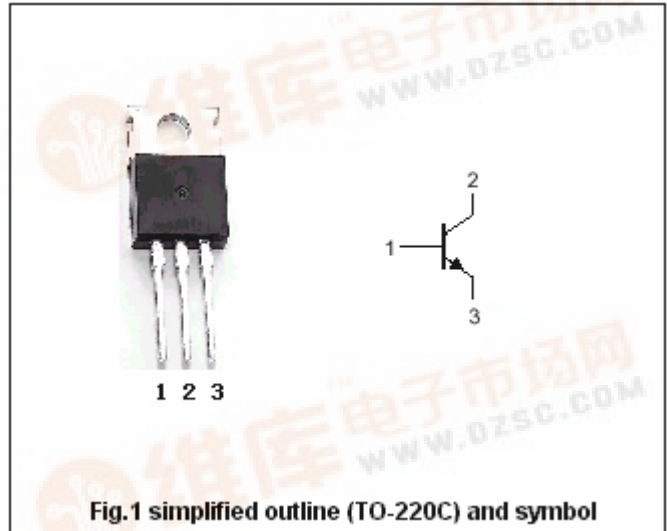
- With TO-220C package
- High current capability

APPLICATIONS

- For audio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	90	V
V _{EBO}	Emitter-base voltage	Open collector	8	V
I _C	Collector current		5	A
P _C	Collector power dissipation	T _C =25	43	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA; R _{BE} =	90			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =5mA; I _E =0	100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =5mA; I _C =0	8			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.4 A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =100V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =0.1A; V _{CE} =2V	60			

固电半导体

INCHANGE SEMICONDUCTOR

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PACKAGE OUTLINE

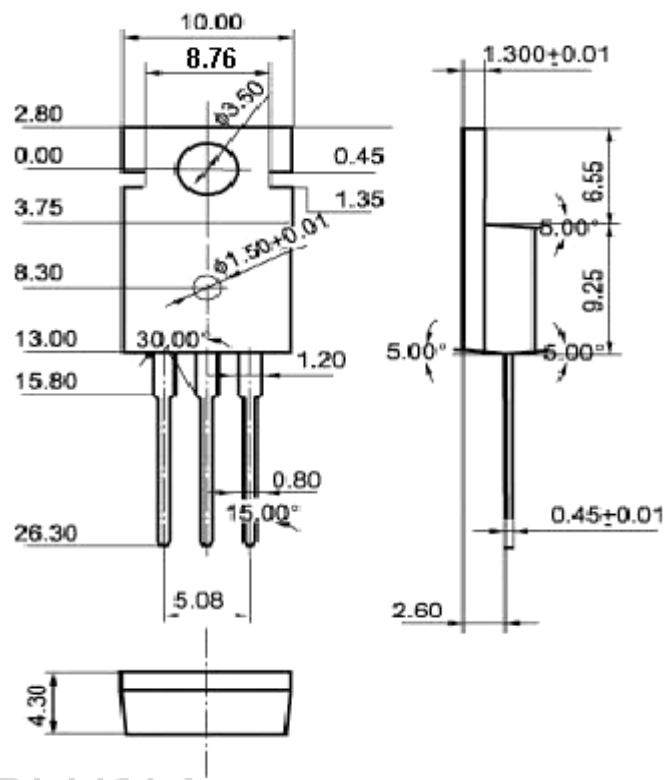


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)